

ABSTRACT

A method of making an electrically operated memory element.
The memory element having a contact in electrical communication
5 with a memory material programmable to at least a first resistance
state and a second resistance state. Preferably, the contact
includes at least a first region having a first resistivity and a
second region having a second resistivity greater than the first
resistivity where the more resistive region is adjacent to the
10 memory material.